

Silicon NPN Power Transistors

2N6486 2N6487 2N6488

DESCRIPTION

With TO-220 package
 Excellent safe operating area
 Complement to type 2N6489 2N6490
 2N6491 respectively

APPLICATIONS

Power amplifier and medium speed
 switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

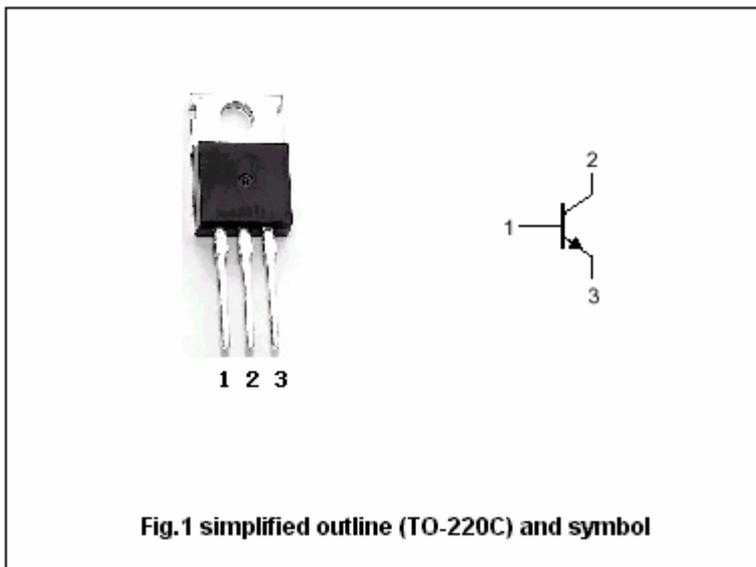


Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N6486	50	V
		2N6487	70	
		2N6488	90	
V _{CEO}	Collector-emitter voltage	2N6486	40	V
		2N6487	60	
		2N6488	80	
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		15	A
I _B	Base current		5	A
P _T	Total power dissipation	T _C =25°C	75	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance from junction to case	1.67	°C/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	2N6486	I _C =0.2A ; I _B =0			V
		2N6487				
		2N6488				
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =5A; I _B =0.5A			1.3	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =15A; I _B =5A			3.5	V
V _{BE-1}	Base-emitter on voltage	I _C =5A ; V _{CE} =4V			1.3	V
V _{BE-2}	Base-emitter on voltage	I _C =15A ; V _{CE} =4V			3.5	V
I _{CEX}	Collector cut-off current V _{BE} =-1.5V	2N6486	V _{CE} =45V; V _{CE} =40V; T _C =150°C			mA
		2N6487				
		2N6488				
I _{CEO}	Collector cut-off current	2N6486	V _{CE} =20V; I _B =0			mA
		2N6487				
		2N6488				
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1.0	mA
h _{FE-1}	DC current gain	I _C =5A ; V _{CE} =4V	20		150	
h _{FE-2}	DC current gain	I _C =15A ; V _{CE} =4V	5			

